Ordering number: ENA0907B

# LV8013T

#### **Bi-CMOS IC**

## Forward/Reverse Motor Driver



http://onsemi.com

#### Overview

LV8013T is a 1ch forward/reverse motor driver IC using D-MOS FET for output stage. As MOS circuit is used, it supports the PWM input. Its features are that the on resistance  $(0.3\Omega \text{ typ})$  and current dissipation are low. It also provides protection functions such as heat protection circuit and reduced voltage detection and is optimal for the motors that need high-current.

#### **Functions**

- 1ch forward/reverse motor driver
- Low power consumption
- Built-in charge pump circuit
- Possible to respond to 3V control voltage and 6V motor voltage device
- Low ON resistance  $0.5\Omega$
- Built-in low voltage reset and thermal shutdown circuit
- Four mode function forward/reverse, brake, stop.

## **Specifications**

**Maximum Ratings** at Ta = 25°C, SGND = PGND = 0V

| Parameter                    | Symbol               | Conditions                     | Ratings                      | Unit |
|------------------------------|----------------------|--------------------------------|------------------------------|------|
| Supply voltage (For load)    | VM max               |                                | -0.5 to 16                   | V    |
| Supply voltage (For control) | V <sub>CC</sub> max  |                                | -0.5 to 6.0                  | V    |
| Output current               | I <sub>O</sub> max   | DC                             | 1.2                          | Α    |
|                              | I <sub>O</sub> peak1 | t ≤ 100ms, f = 5Hz             | 2.0                          | Α    |
|                              | I <sub>O</sub> peak2 | t ≤ 10ms, f = 5Hz              | 3.8                          | Α    |
| Input voltage                | V <sub>IN</sub> max  |                                | -0.5 to V <sub>CC</sub> +0.5 | V    |
| Allowable power dissipation  | Pd max               | Mounted on a specified board * | 800                          | mW   |
| Operating temperature        | Topr                 |                                | -20 to +75                   | °C   |
| Storage temperature          | Tstg                 |                                | -55 to +150                  | °C   |

<sup>\*</sup>Specified board:  $30\text{mm} \times 50\text{mm} \times 1.6\text{mm}$ , glass epoxy board.

Caution 2) Even when the device is used within the range of absolute maximum ratings, as a result of continuous usage under high temperature, high current, high voltage, or drastic temperature change, the reliability of the IC may be degraded. Please contact us for the further details.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Caution 1) Absolute maximum ratings represent the value which cannot be exceeded for any length of time.

#### LV8013T

## Allowable Operating Conditions at Ta = 25°C, SGND = PGND = 0V

| Parameter                    | Symbol                | Conditions | Ratings              | Unit |
|------------------------------|-----------------------|------------|----------------------|------|
| Supply voltage (For load)    | VM                    |            | 2.0 to 15.0          | V    |
| Supply voltage (For control) | V <sub>CC</sub>       |            | 2.7 to 5.5           | V    |
| Input signal voltage         | V <sub>IN</sub>       |            | 0 to V <sub>CC</sub> | V    |
| Input signal frequency       | f max                 | Duty = 50% | 200                  | kHz  |
| Capacitor for charge pump    | C1, C2,<br>CVG1, CVG2 |            | 0.001 to 0.1         | μF   |

## **Electrical Characteristics** at Ta = 25 °C, $V_{CC} = 5.0V$ , VM = 12.0V, SGND = PGND = 0V, unless especially specified.

| Parameter                              |                   | Symbol            | Conditions                                       | Re-   | Ratings             |      |                     | Unit |
|--|-------------------|-------------------|--|-------|---------------------|------|---------------------|------|
|  |                   | Symbol Conditions |  | marks | min                 | typ  | max                 | Unit |
| Supply current for load at standby 1   |                   | IM1               | EN = 0V  | 1     |                     |      | 1.0                 | μΑ   |
| Supply current for standby 2           | or load at        | IM2               | V <sub>CC</sub> = 0V, Each input = 0V            | 1     |                     |      | 1.0                 | μΑ   |
| Supply current for standby             | or control at     | ICO               | EN = 0V, IN1 = IN2 = 0V                          | 2     | 12.5                | 25   | 50                  | μА   |
| Current drain du                       | uring operation 1 | IC1               | V <sub>CC</sub> = 3.3V, EN = 3.3V, VG at no load | 3     |                     | 0.6  | 1.0                 | mA   |
| Current drain du                       | uring operation 2 | IC2               | V <sub>CC</sub> = 5.0V, EN = 5V, VG at no load   | 3     |                     | 0.7  | 1.2                 | mA   |
| H-level input vol                      | Itage             | V <sub>IH</sub>   | 2.7V ≤ V <sub>CC</sub> ≤ 5.5V                    |       | 0.6×V <sub>CC</sub> |      | V <sub>CC</sub>     | V    |
| L-level input vol                      | tage              | V <sub>IL</sub>   | 2.7V ≤ V <sub>CC</sub> ≤ 5.5V                    |       | 0                   |      | 0.2×V <sub>CC</sub> | V    |
| H-level input cui                      | rrent             | lН                | V <sub>IN</sub> = 5V                             | 4     | 12.5                | 25   | 50                  | μΑ   |
| L-level input cur<br>(IN1, IN2, TIN)   | rent              | IIL               | V <sub>IN</sub> = 0V                             | 4     | -1.0                |      |                     | μΑ   |
| Pull-up resistand                      | ce (EN)           | RUP               |  | 4     | 100                 | 200  | 400                 | kΩ   |
| Pull-down resistance<br>(EN)           |                   | RDN               |  | 4     | 100                 | 200  | 400                 | kΩ   |
| Output ON resistance                   |                   | RON               | Sum of ON resistances at top and bottom          | 5     |                     | 0.3  | 0.5                 | Ω    |
| Charge pump voltage1                   |                   | VG1               | V <sub>CC</sub> ×2 - 5.4V CLAMP circuit          | 6     | 5.15                | 5.4  | 5.65                | V    |
| Charge pump vo                         | oltage2           | VG2               | VM + VG1 Voltage raising circuit                 | 6     | 17.1                | 17.4 | 17.6                | V    |
| Low-voltage det voltage                | tection operation | VCS               | V <sub>CC</sub> voltage                          | 7     | 2.1                 | 2.25 | 2.4                 | V    |
| Thermal shutdown operation temperature |                   | Tth               | Design guarantee                                 | 8     | 150                 | 180  | 210                 | °C   |
| Charge pump ca                         | apacity 1         | VG1LOAD           | IG1 = 500μA                                      | 9     | 5.0                 | 5.3  |                     | V    |
| Charge pump ca                         | apacity 2         | VG2LOAD           | IG2 = 500μA                                      | 9     | 16.0                | 16.5 |                     | V    |
| IG current dissipation (Fin = 20kHz)   |                   | IG                |  | 10    |                     |      | 350                 | μА   |
| Charge pump start time                 |                   | TVG               | CVG = 0.1μF                                      | 11    |                     |      | 1.0                 | ms   |
| Output                                 | Turn on time      | TPLH              |  | 12    |                     | 0.5  | 1.0                 | μs   |
| block                                  | Turn off time     | TPHL              |  | 12    |                     | 0.5  | 1.0                 | μs   |
| TOUT                                   | Turn on time      | TON               | C = 500pF  | 12    |                     | 0.5  | 20                  | μs   |
|  | Turn off time     | TOFF              | C = 500pF  | 12    |                     | 0.5  | 20                  | μs   |
| TOUT output voltage H                  |                   | ТОН               | C = 500pF  |       | VG2-0.1             | VG2  |                     | V    |
| TOUT output vo                         | oltage L          | TOL               | C = 500pF  |       |                     | 0.05 | 0.1                 | V    |

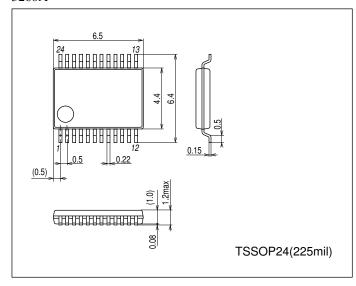
<sup>\*</sup> Design guarantee : This characteristics is not measured. Refer to next page for remarks.

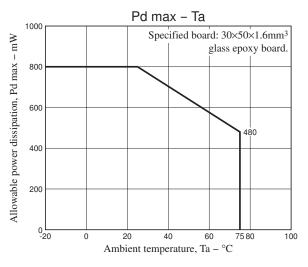
#### Remarks

- 1. It shows current dissipation of VM pin in output OFF state.
- 2. It shows current dissipation of V<sub>CC</sub> pin in stand-by state. (The standard current depends on EN pin pull-down resistor.)
- 3. It shows current dissipation of  $V_{CC}$  pin in state of EN = 5V (stand-by), including current dissipation of  $V_{CC}$  pin.
- 4. IN1, IN2 and TIN pin are built-in pull-down resistor, EN pin is built-in pull-up resistor.
- 5. It shows sum of upper and lower saturation voltages of OUT pin.
- 6. It controls charge-pump oscillation and makes specified voltage.
- 7. When low voltage is detected, the lower output is turned OFF.
- 8. When thermal protection circuit is activated, the lower output is turned OFF. When the heat temperature is fallen, it is turned ON again.
- 9. IG (VG pin load current) =  $500\mu$ A
- 10. It shows VG pin current dissipation in state of PWM input for IN pin.
- 11. It specifies start-up time from 10% to 90% when VG is in non-load state (when setting the capacitor between VG and GND to  $0.1\mu F$  and  $V_{CC}$  is 5V).
- 12. It specifies 10% to 90% for start-up and 90% to 10% for shut-down.

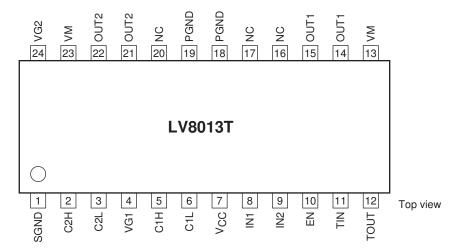
## **Package Dimensions**

unit : mm (typ) 3260A

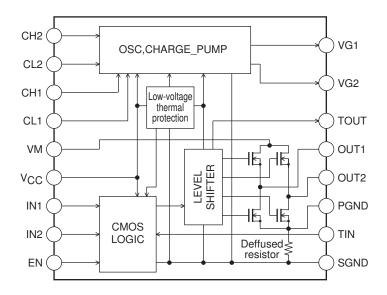




#### Pin Assignment



## **Block Diagram**



## **Truth Table**

| EN | IN1 | IN2 | TIN     | OUT1 | OUT2    | TOUT | Charge Pump | Mode    |
|----|-----|-----|---------|------|---------|------|-------------|---------|
|    | Н   | Н   | -       | L    | L       | -    |             | Brake   |
|    | Н   | L   | -       | Н    | L       | -    |             | Forward |
|    | L   | Н   | - L н - | ON   | Reverse |      |             |         |
| Н  | L   | L   | -       | Z    | Z       | -    | ON          | Standby |
|    | -   | -   | L       | -    | -       | L    |             | Tr-OFF  |
|    | -   | -   | Н       | -    | -       | Н    |             | Tr-ON   |
| L  | -   | -   | -       | L    | L       | L    | OFF         | Standby |

- : Don't care, Z : High-Impedance

- Current drain becomes zero in the standby mode. (Leak current from EN pin is excluded)
- The output side becomes OFF, with motor drive stopped, during voltage reduction and thermal protection. Also, the charge of VG2 is discharged with an internal circuit at decreasing voltage.

### **Pin Function**

| Pin No.      | Pin name          | Function  | Equivalent circuit |
|--------------|-------------------|---|--------------------|
| 6            | C1L               | Voltage raising capacitor connection pin.   | C1L C              |
| 5            | C1H               | Voltage raising capacitor connection pin.   | C1H VG1            |
| 8<br>9<br>11 | IN1<br>IN2<br>TIN | Driver output changeover.      TOUT output control pin. (Built-in pull-down resistor) | VCC                |

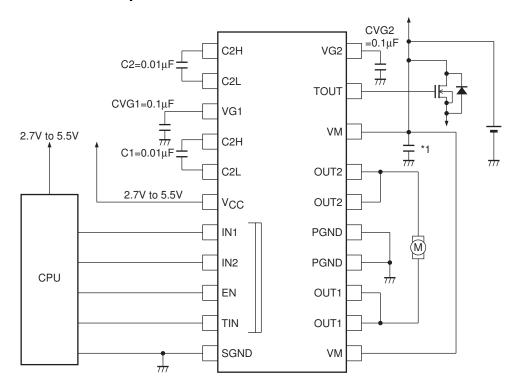
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| Pin No.                          | Pin name                                     | Function   | Equivalent circuit                  |
|----------------------------------|--|--|-------------------------------------|
| 10                               | EN   | Logic enable pin.  |                                     |
| 10                               | ĽΝ   | (Built-in pull-up resistor)  | V <sub>CC</sub>                     |
| 14<br>15<br>21<br>22<br>18<br>19 | OUT1<br>OUT1<br>OUT2<br>OUT2<br>PGND<br>PGND | Driver output pin.   | OUT1 OUT2                           |
| 12                               | TOUT   | Voltage raising output pin.  | VG2                                 |
| 13<br>23                         | VM<br>VM                                     | Motor power supply. (both terminals to be connected)   |                                     |
| 7                                | V <sub>CC</sub>                              | Logic power supply.  |                                     |
| 4                                | VG1  | Voltage raising circuit 1.  V <sub>CC</sub> × 2  Clamped to 5.4V   | VG1<br>C1H 0.1μF<br>0.01μF<br>C1L 7 |
| 24 2 3                           | VG2<br>C2H<br>C2L                            | Voltage raising circuit 2. VM + VG1 Voltage raising capacitor connection pin. VG2 is discharged in abnormal. | VM<br>C2H<br>0.01μF<br>C2L          |
| 1                                | SGND   | Logic GND  |                                     |
| 18                               | PGND   | Driver GND   |                                     |
| 19                               | PGND   | (both terminals to be connected)   |                                     |

## **Application Circuit Example**



\*1 : Connect a kickback absorption capacitor directly near IC. Coil kick-back may cause rise of the voltage of VM line, and the voltage exceeding the maximum rating may be applied momentarily, resulting in deterioration or damage of IC.

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